

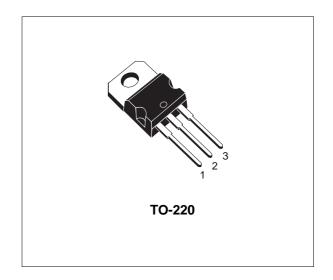
# **BU931T**

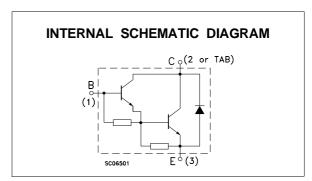
# HIGH VOLTAGE IGNITION COIL DRIVER NPN POWER DARLINGTON TRANSISTOR

- VERY RUGGED BIPOLAR TECHNOLOGY
- HIGH OPERATING JUNCTION TEMPERATURE

#### **APPLICATIONS**

 HIGH RUGGEDNESS ELECTRONIC IGNITIONS





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	500	V
$V_{CEO}$	Emitter-Base Voltage (I <sub>B</sub> = 0)	400	V
$V_{EBO}$	Emitter-Base Voltage (I <sub>C</sub> = 0)	5	V
Ic	Collector Current	10	A
I <sub>CM</sub>	Collector Peak Current	15	А
I <sub>B</sub>	Base Current	1	А
I <sub>BM</sub>	Base Peak Current	5	А
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	125	W
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
Tj	Max. Operating Junction Temperature	175	°C

October 2003 1/6

#### THERMAL DATA

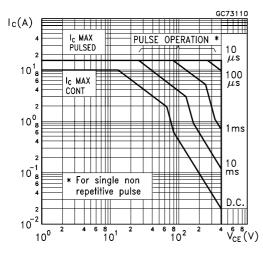
R <sub>thj-case</sub> Thermal Resistance Junction-case Max	1.2	°C/W
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## **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

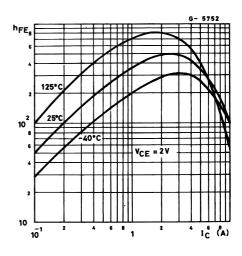
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 500 V V <sub>CE</sub> = 500 V T <sub>C</sub> = 125 °C			100 0.5	μA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	$V_{CE} = 450 \text{ V}$ $V_{CE} = 450 \text{ V}$ $T_{C} = 125 ^{\circ}\text{C}$			100 0.5	μA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			20	mA
V <sub>CEO(SUS)</sub> *	Collector-Emitter Saturation Voltage (I <sub>B</sub> = 0)	$I_C$ = 100 mA $$ L = 10 mH $$ $I_B$ = 0 $$ $V_{CLAMP}$ = 400 V (see fig.4)	400			V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	$I_C = 7 \text{ A}$ $I_B = 70 \text{ mA}$ $I_C = 8 \text{ A}$ $I_B = 100 \text{ mA}$			1.6 1.8	V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	$I_C = 7 \text{ A}$ $I_B = 70 \text{ mA}$ $I_C = 8 \text{ A}$ $I_B = 100 \text{ mA}$			2.2 2.4	V V
h <sub>FE</sub> *	DC Current Gain	Ic = 5 A VcE = 10 V	300			
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 10 A			2.5	V
	Functional Test	$V_{CC} = 24 \text{ V } V_{clamp} = 400 \text{ V } L=7 \text{ mH}$ (see fig. 1)	8			А
t <sub>s</sub>	INDUCTIVE LOAD Storage Time Fall Time	$\begin{split} &V_{CC}=12~V~V_{clamp}=300~V~L=7~mH\\ &I_{C}=7~A~I_{B}=70~mA\\ &V_{BE}=0~~R_{BE}=47~\Omega\\ &(\text{see fig. 3}) \end{split}$		15 0.5		μs μs

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

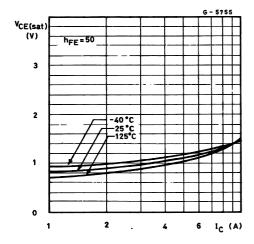
#### Safe Operating Area



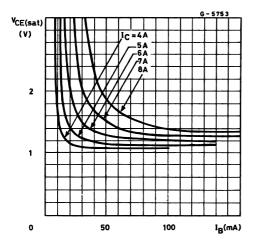
#### DC Current Gain



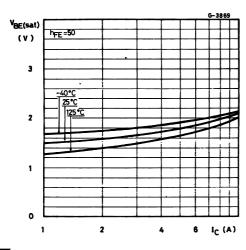
#### Collector Emitter Saturation Voltage



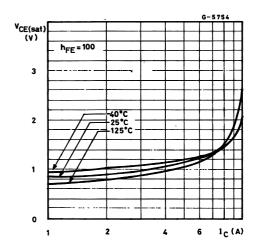
#### Collector Emitter Saturation Voltage



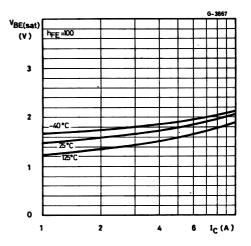
Base Emitter Saturation Voltage



#### Collector Emitter Saturation Voltage



Base Emitter Saturation Voltage



#### Switching Time Inductive Load

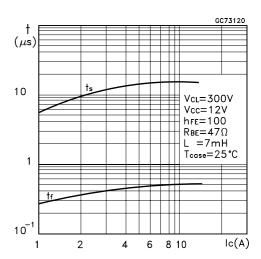


FIGURE 1: Functional Test Circuit

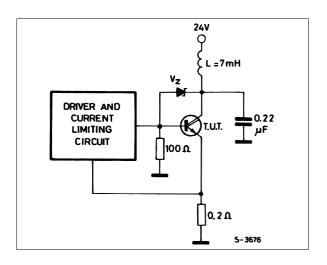


FIGURE 3: Switching Time Test Circuit

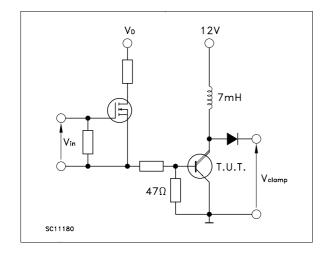


FIGURE 2: Functional Test Waveforms

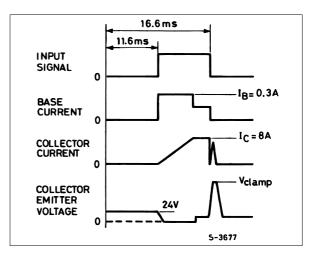
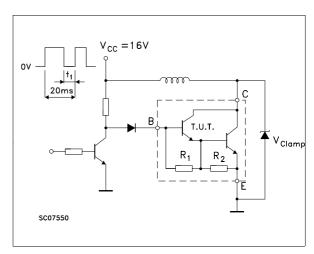
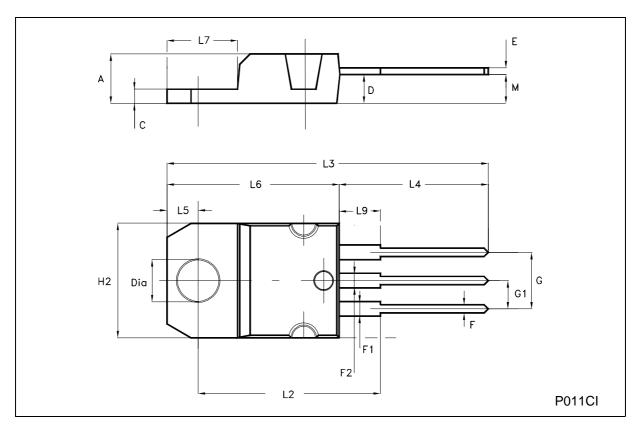


FIGURE 4: Sustaining Voltage Test Circuit



## **TO-220 MECHANICAL DATA**

DIM.	mm					
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



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